2SC1212, 2SC1212A

Silicon NPN Epitaxial

HITACHI

Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings (Ta = 25° C)

		Ratings			
Item	Symbol	2SC1212	2SC1212A	Unit	
Collector to base voltage	V _{CBO}	50	80	V	
Collector to emitter voltage	V _{CEO}	50	80	V	
Emitter to base voltage	V _{EBO}	4	4	V	
Collector current	Ι _c	1	1	А	
Collector power dissipation	Pc	0.75	0.75	W	
	P _c *1	8	8	W	
Junction temperature	Tj	150	150	°C	
Storage temperature	Tstg	-55 to +150	-55 to +150	°C	

Note: 1. Value at $T_c = 25^{\circ}C$



2SC1212, 2SC1212A

Electrical Characteristics (Ta = 25°C)

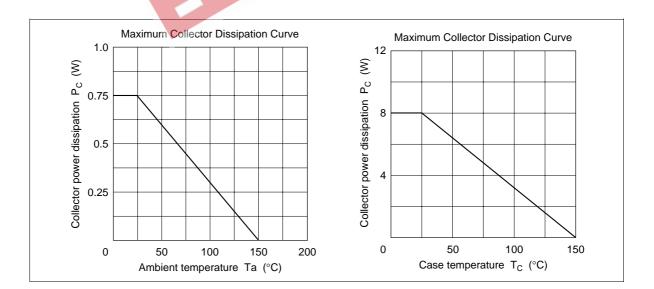
		2SC1	212		2SC1212A				
ltem	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	50	_	_	80	_	_	V	$I_{c} = 1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\rm (BR)CEO}$	50	_	_	80	_		V	I_{c} = 10 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	4	_		4	_	_	V	$I_{\rm E} = 1$ mA, $I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	—	5	—	—	5	μΑ	$V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0$
DC current tarnsfer ratio	h_{FE}^{*1}	60	—	200	60	—	200		$V_{ce} = 4 \text{ V}, I_c = 50 \text{ mA}$
	h _{FE}	20	—	—	20	—	-	2_	$V_{ce} = 4 V, I_c = 1 A$ (pulse test)
Base to emitter voltage	V_{BE}	—	0.65	1.0	—	0.65	1.0	V	$V_{ce} = 4 \text{ V}, \text{ I}_{c} = 50 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$		0.75	1.5	30 9	0.75	1.5	V	$I_{c} = 1 \text{ A}, I_{B} = 0.1 \text{ A}$ (pulse test)
Gain bandwidth product	f _T	_	160		<u>191</u>	160	1.	MHz	V_{ce} = 4 V, I_c = 30 mA

Note: 1. The 2SC1212 and 2SC1212A are grouped by h_{FE} as follows.

В

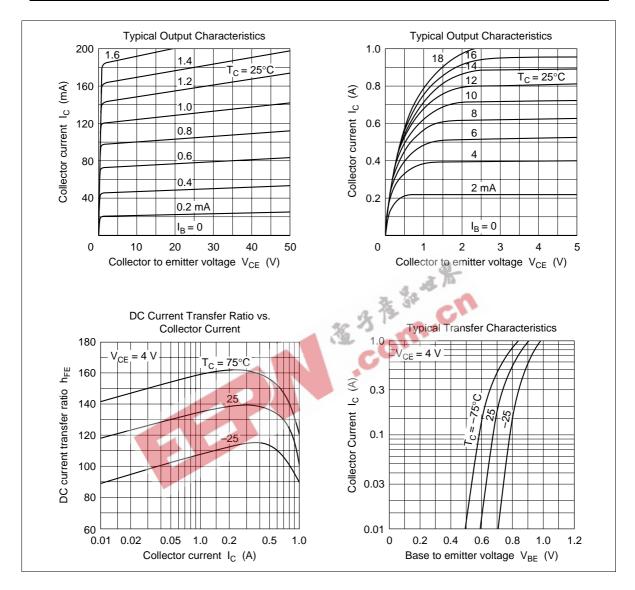
60 to 120 100 to 200

С

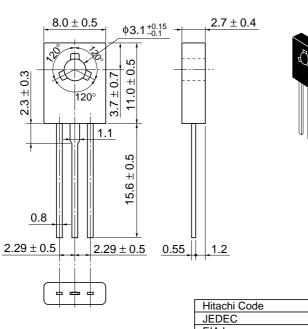


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2SC1212, 2SC1212A







Unit: mm

Hitachi Code	TO-126 Mod
JEDEC	
EIAJ	_
Weight (reference value)	0.67 g

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